Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Material:

Metal

Overall Length:

4.327 inches

Overall Diameter:

1.443 inches

Mounting Facility Quantity:

1

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Threaded stud

Overall Width Across Flats:

Between 1.218 inches and 1.250 inches

Thread Size:

0.750 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

700.0 forward voltage, peak and 700.0 repetitive peak reverse voltage, peak total value, gate terminal open-circuited and 840.0

nonrepetitive peak reverse voltage, peak total value, gate terminal open-circuited

Current Rating Per Characteristic:

3500.00 amperes source cutoff current peak

Power Rating Per Characteristic:

10.0 watts small-signal input power, common-collector universal

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius ambient air

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 threaded stud and 3 insulated wire lead w/terminal lug

Shelf Life:

N/a

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Unit Of Measure:
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Demilitarization:
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No

Fiig:

A110a0